# imall

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**ZXMP3A17E6** 

#### **Product Summary**

V <sub>(BR)DSS</sub>	Max R <sub>DS(ON)</sub>	Max I <sub>D</sub> T <sub>A</sub> = +25°C (Note 6)
-30V	70mΩ @ V <sub>GS</sub> = -10V	-4A

## **Description and Applications**

This new generation of TRENCH MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

- DC DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

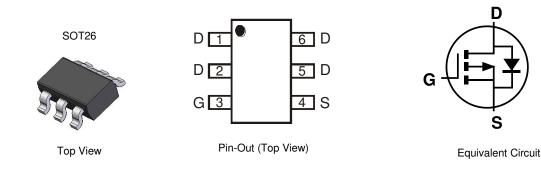
#### **30V P-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features and Benefits**

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.016 grams (Approximate)



#### Ordering Information (Note 4)

Part Number	Marking	Reel Size (inch)	Tape Width (mm)	Quantity Per Reel
ZXMP3A17E6TA	317	7	8	3000
ZXMP3A17E6TC	317	13	8	10,000

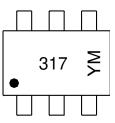
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



4

 $\begin{array}{l} 317 = Product \mbox{ Type Marking Code} \\ YM = Date \mbox{ Code Marking} \\ Y \mbox{ or } \overline{Y} = Year \mbox{ (ex: C = 2015)} \\ M \mbox{ or } \overline{M} = M \mbox{ onth (ex: 9 = September)} \end{array}$ 

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Date Code	Key
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Code

Notes:

Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н			J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

5

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# Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit	
Drain-Source Voltage			V <sub>DSS</sub>	-30	V	
Gate-Source Voltage			V <sub>GS</sub>	±20	V	
		T <sub>A</sub> = +25°C (Note 6)		-4.0		
Continuous Drain Current	$V_{GS} = -10V$	T <sub>A</sub> = +70°C (Note 6)	ID	-3.2	А	
		T <sub>A</sub> = +25°C (Note 5)		-3.2		
Pulsed Drain Current (Note 7)			IDM	-14.4	А	
Continuous Source Current	(Body Diode) (N	ote 6)	IS	-2.5	А	
Pulsed Source Current (Body Diode) (Note 7)			I <sub>SM</sub>	-14.4	Α	

#### **Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at $T_A$ = +25°C (Note 5) Linear derating factor	PD	1.1 8.8	W mW/°C
Power Dissipation at $T_A$ = +25°C (Note 6) Linear Derating Factor	PD	1.7 13.6	W mW/°C
Junction to Ambient (Note 5)	R <sub>0</sub> JA	113	°C/W
Junction to Ambient (Note 6)	R <sub>0</sub> JA	73	°C/W
Operating and Storage Temperature Range	TJ, T <sub>STG</sub>	-55 to +150	°C

 Notes:
 5. For a device surface mounted on 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.

 6. For a device surface mounted on FR-4 PCB measured at t≦5 secs.

7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

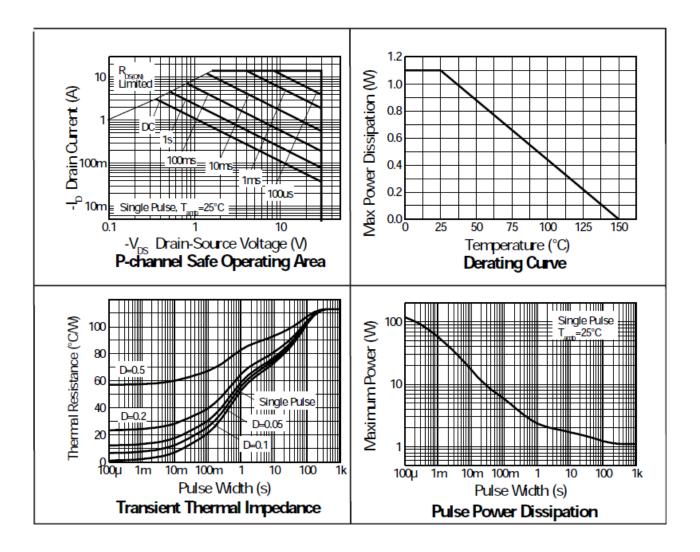
Characteristic	Cumhal	Min	Turn	Мах	Unit	Test Condition	
	Symbol	MIN	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS			r	r			
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	-30	-	-	V	$I_{D} = -250 \mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	-0.5	μA	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Body Leakage	IGSS	-	-	100	nA	$V_{GS}=\pm 20V, \ V_{DS}=0V$	
Gate-Source Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	-	-	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Static Drain-Source On-State Resistance (Note 8)				0.070	Ω	$V_{GS} = -10V, I_D = -3.2A$	
	R <sub>DS(ON)</sub>	-	-	0.110	12	V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-2.5A	
Forward Transconductance (Notes 8 &10)	<b>g</b> <sub>fs</sub>	-	6.4	-	S	V <sub>DS</sub> = -15V, I <sub>D</sub> =-3.2A	
Diode Forward Voltage (Note 8)	V <sub>SD</sub>	-	-0.85	-1.2	V	$T_{J}$ = +25°C , $I_{S}$ = -2.5A, $V_{GS}$ = 0V	
DYNAMIC CHARACTERISTICS	-						
Input Capacitance (Note 10)	Ciss	-	630	-	pF		
Output Capacitance (Note 10)	Coss	-	113	-	pF	−V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V −f = 1MHz	
Reverse Transfer Capacitance (Note 10)	C <sub>rss</sub>	-	78	-	pF		
Gate Charge (Notes 9 &10)	Qg	-	8.28	-	nC	$V_{GS} = -5V, V_{DS} = -15V$ $I_D = -3.2A$	
Total Gate Charge (Notes 9 &10)	Qg	-	15.8	-	nC		
Gate-Source Charge (Notes 9 &10)	Qgs	-	1.84	-	nC	$V_{GS} = -10V, V_{DS} = -15V$	
Gate-Drain Charge (Notes 9 &10)	Q <sub>gd</sub>	-	2.8	-	nC	$-I_{\rm D} = -3.2$ A	
Turn-On Delay Time (Notes 9 &10)	t <sub>D(ON)</sub>	-	1.74	-	ns		
Turn-On Rise Time (Notes 9 &10)	t <sub>R</sub>	-	2.87	-	ns	V <sub>DD</sub> = -15V, V <sub>GS</sub> = -10V	
Turn-Off Delay Time (Notes 9 &10)	t <sub>D(OFF)</sub>	-	29.2	-	ns	$I_{\rm D} = -1A, R_{\rm G} = 6.0\Omega$	
Turn-Off Fall Time (Notes 9 &10)	t <sub>F</sub>	-	8.72	-	ns	7	
Reverse Recovery Time (Note 10)	t <sub>RR</sub>	-	19.5	-	ns	T <sub>J</sub> = +25°C, I <sub>F</sub> =-1.7A,	
Reverse Recovery Charge (Note 10)	Q <sub>RR</sub>	-	16.3	-	nC	di/dt= 100A/µs	

Notes: 8. Measured under pulsed conditions. Width=300 $\mu$ s. Duty cycle ≤ 2%

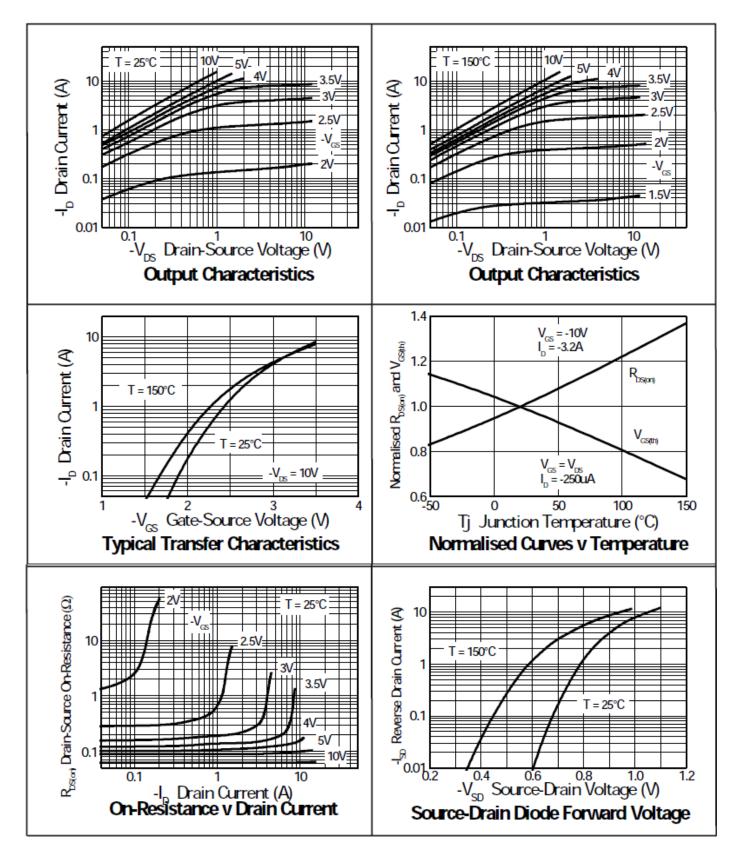
9. Switching characteristics are independent of operating junction temperature.

10. For design aid only, not subject to production testing.

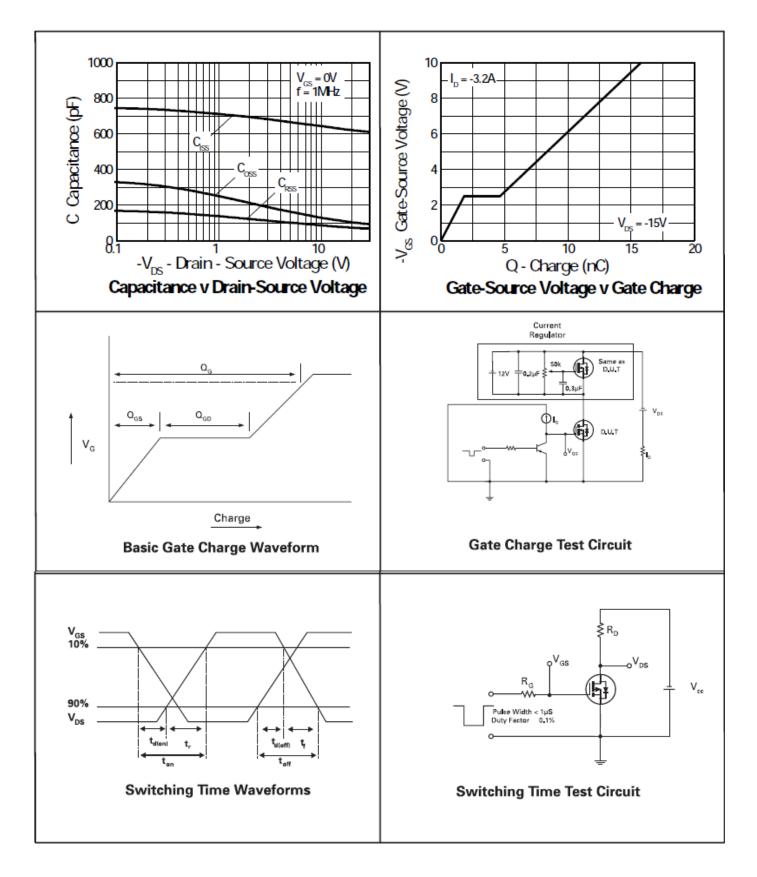








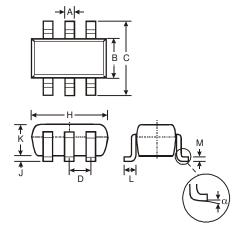






## **Package Outline Dimensions**

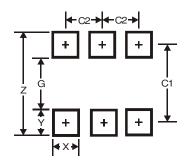
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26						
Dim	Dim Min Max						
Α	0.35	0.50	0.38				
В	1.50	1.70	1.60				
С	2.70	3.00	2.80				
D	_	_	0.95				
Н	2.90	3.10	3.00				
J	0.013	0.10	0.05				
Κ	K 1.00 1.30 1.1						
L	L 0.35 0.55 0.40						
М	M 0.10 0.20 0.						
α 0° 8° —							
aii d	imensi	ons in	mm				

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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